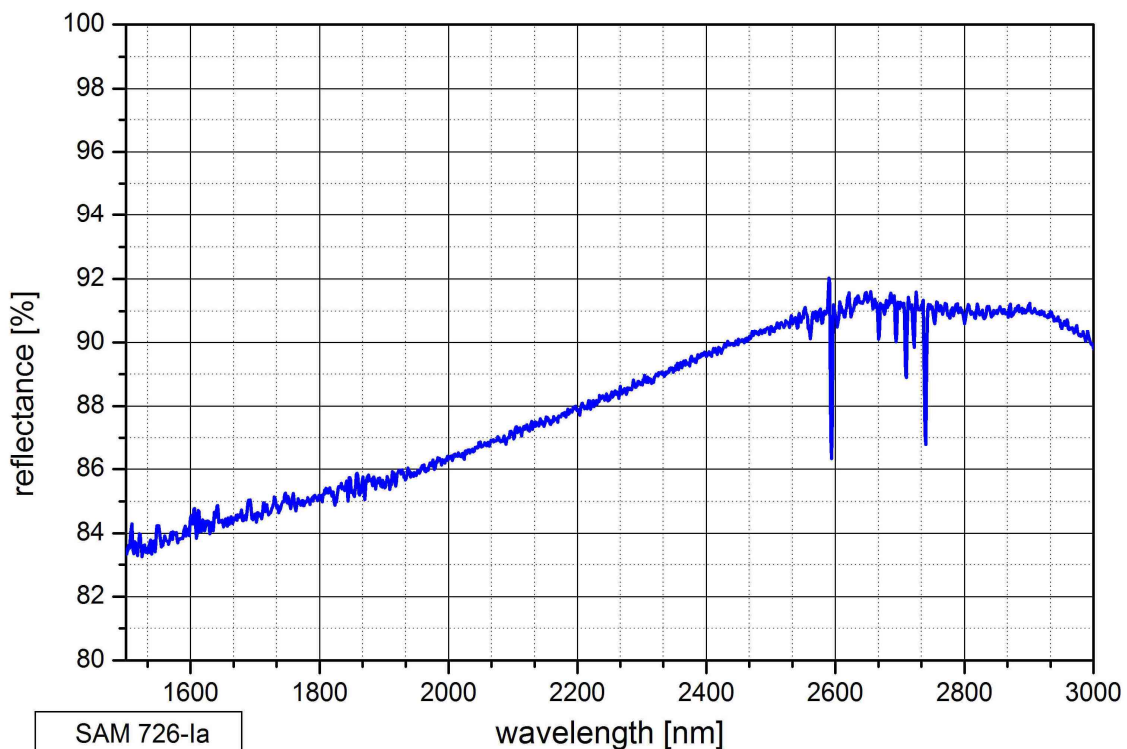


SAM™ Data Sheet SAM-2900-9-10ps-x, $\lambda = 2900 \text{ nm}$

| | |
|---|--|
| Laser wavelength | $\lambda = 2900 \text{ nm}$ |
| High reflection band | $\lambda = 2400 \dots 3000 \text{ nm}$ |
| Absorbance | $A_0 = 9 \%$ |
| Modulation depth | $\Delta R = 4 \%$ |
| Non-saturable loss | $A_{ns} = 5 \%$ |
| Saturation fluence | $\Phi_{sat} = 150 \mu\text{J}/\text{cm}^2$ |
| Relaxation time constant | $\tau \sim 10 \text{ ps}$ |
| Damage threshold | $\Phi_{sat} = 2 \text{ mJ}/\text{cm}^2$ |
| Chip area | 4.0 mm x 4.0 mm; other dimensions on request |
| Chip thickness | 620 μm |
| Reverse design | the absorber layer is illuminated through the 620 μm thick GaAs wafer |
| Mounting option x denotes the type of mounting as follows: | |
| x = 0 | unmounted |
| x = 12.7 g | glued on a copper heat sink with 12.7 mm diameter |
| x = 25.4 g | glued on a copper heat sink with 25.4 mm diameter |

Low intensity spectral reflectance



Reverse design of the SAM-2900-9-x-10ps

